

T814 3400-54-65

Key Parameters

V_{DSM}	5400~6500	V
$I_{T(AV)}$	3400	A
I_{TSM}	71	kA
V_{TO}	1.13	V
r_T	0.185	mΩ

Applications

- SVC
- Motor drive
- Industry converter

Features

- Double-side cooling
- High power capability
- Low loss

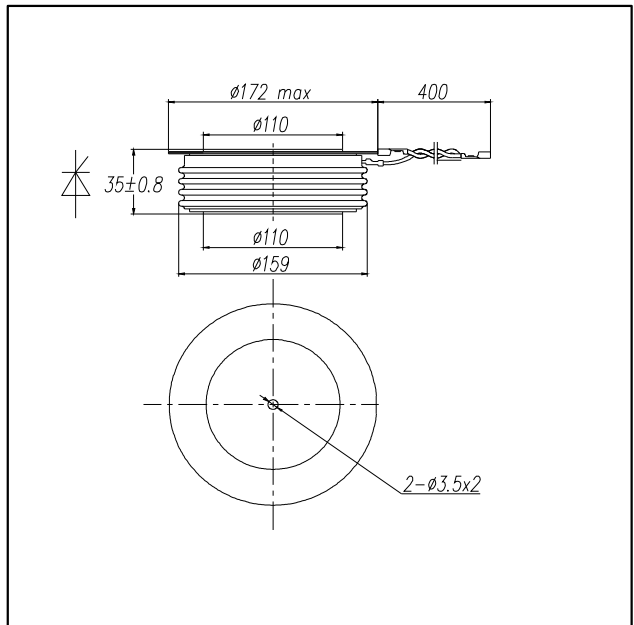
Thermal & Mechanical Data

Symb.	Parameter	Min	Type	Max	Unit
R_{jc}	Thermal Resistance Junction to Case	-	-	0.004	K / W
R_{cs}	Thermal Resistance Case to Heatsink	-	-	0.0008	K / W
T_{vj}	Junction Temperature	-40	-	110	°C
T_{stg}	Storage Temperature	-40	-	140	°C
F	Mounting Force	80	-	132	kN
m	Weight	-	3.5	-	kg
HCRP	Creep distance	34	-	-	mm

Voltage Ratings

Device Type	$V_{DSM}/V_{RSM}(V)$	Test Conditions
T814 3400-54	5400	$T_{vj} = 110\text{ °C}$
T814 3400-58	5800	$I_{DRM} = 700\text{ mA}$
T814 3400-62	6200	$I_{RRM} = 700\text{ mA}$
T814 3400-65	6500	$V_{DM} = V_{DRM}, V_{RM} = V_{RRM}$ $t_p = 10\text{ ms}$ $V_{DRM} = V_{DSM} - 900$ $V_{RRM} = V_{RSM} - 900$

Outline



Current Ratings

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
$I_{T(AV)}$	Mean On-State Current	Half Sine Wave, $T_C = 70\text{ °C}$	-	-	3400	A
$I_{T(RMS)}$	RMS On-State Current	$T_C = 70\text{ °C}$	-	-	5338	A
I_{TSM}	Surge (non-repetitive) On-State Current	10ms, Half Sine Wave, $T_C = 110\text{ °C}, V_R = 0$	-	-	71	kA
I^2t	Limiting load integral	Sine Wave, 10ms	-	-	2521	$10^4 A^2s$

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Characteristics

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
V_{TM}	Peak on-state voltage	$T_{vj} = 110\text{ }^{\circ}\text{C}$, $I_{TM} = 3000\text{ A}$	-	-	1.69	V
I_{DRM}	Forward leakage current	$T_{vj} = 110\text{ }^{\circ}\text{C}$, V_{DRM}	-	-	700	mA
I_{RRM}	Reverse leakage current	$T_{vj} = 110\text{ }^{\circ}\text{C}$, V_{RRM}	-	-	700	mA
V_{TO}	Threshold voltage	$T_{vj} = 110\text{ }^{\circ}\text{C}$	-	-	1.13	V
r_T	Slope resistance	$T_{vj} = 110\text{ }^{\circ}\text{C}$	-	-	0.185	m Ω
I_H	Holding current	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	-	200	mA
I_L	Latching current	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	-	1000	mA

Dynamic Parameters

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
dv/dt	Critical rate of rise of off-state voltage	$T_{vj} = 110\text{ }^{\circ}\text{C}$, $0.67V_{DRM}$	2000	-	-	V/ μ s
di/dt	Critical rate of rise of on-state current	$T_{vj} = 110\text{ }^{\circ}\text{C}$, $V_{DM} = 0.67V_{DRM}$, $I_{TM} = 4000\text{ A}$, $f = 1\text{ Hz}$	-	-	1000	A/ μ s
		$I_{FG} = 2\text{ A}$, $t_r = 0.5\text{ }\mu\text{s}$, $f = 50\text{ Hz}$	-	-	200	
t_d	Delay time	$T_{vj} = 25\text{ }^{\circ}\text{C}$, $V_{DM} = 0.5V_{DRM}$, $I_{TM} = 4000\text{ A}$, $I_{FG} = 2\text{ A}$, $t_r = 0.5\text{ }\mu\text{s}$	-	-	3.0	μ s
t_q	Turn-off time	$T_{vj} = 110\text{ }^{\circ}\text{C}$, $V_{DM} = 0.67V_{DRM}$, $dv/dt = 20\text{ V}/\mu\text{s}$, $V_R = 200\text{ V}$, $di_T/dt = -1.5\text{ A}/\mu\text{s}$, $I_T = 2000\text{ A}$	-	1000	-	μ s
Q_{rr}	Recovery Charge	$T_{vj} = 110\text{ }^{\circ}\text{C}$, $di_T/dt = -1.5\text{ A}/\mu\text{s}$, $V_R = 200\text{ V}$, $I_T = 2000\text{ A}$	-	-	5750	μ C
I_{rr}	Reverse recovery current		-	-	95	A

Gate Parameters

Symb.	Parameter	Test Conditions	Min	Type	Max	Unit
I_{GT}	Gate trigger current	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	-	400	mA
V_{GT}	Gate trigger voltage	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-	-	2.6	V
V_{GD}	Gate non-trigger voltage	$T_{vj} = 110\text{ }^{\circ}\text{C}$, $V_D = 0.4V_{DRM}$	0.3	-	-	V
V_{FGM}	Peak forward gate voltage		-	-	12	V
V_{RGM}	Peak reverse gate voltage		-	-	5	V
I_{FGM}	Peak forward gate current		-	-	4	A
P_{GM}	Gate power losses		-	-	20	W
$P_{G(AV)}$	Gate power losses (mean)		-	-	4	W

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Max. on-state characteristic model

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

	25 °C	110 °C
A	1.501590	0.371622
B	-0.043702	0.10741200
C	0.0000911	0.0001477
D	0.0074264	0.0002108

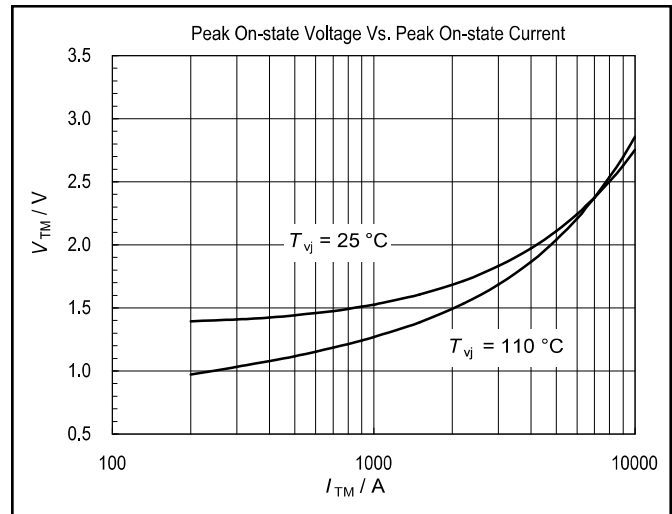


Fig1. Peak On-state Voltage Vs. Peak On-state Current

Transient thermal impedance function
(double side cooled)

$$R_{thjc}(t) = \sum_{i=1}^n R_{thi} \cdot \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

i	1	2	3	4
R _{thi} (K/kW)	2.695	0.814	0.33	0.162
τ _i (s)	0.9692	0.1332	0.0177	0.0042

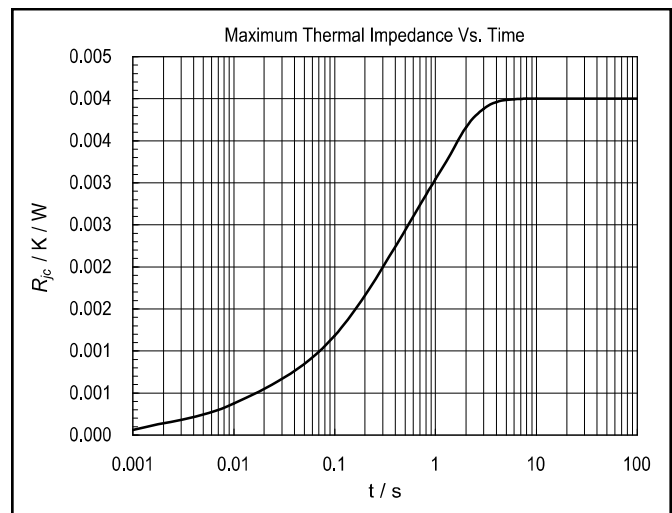


Fig2. Maximum Thermal Impedance Vs. Time

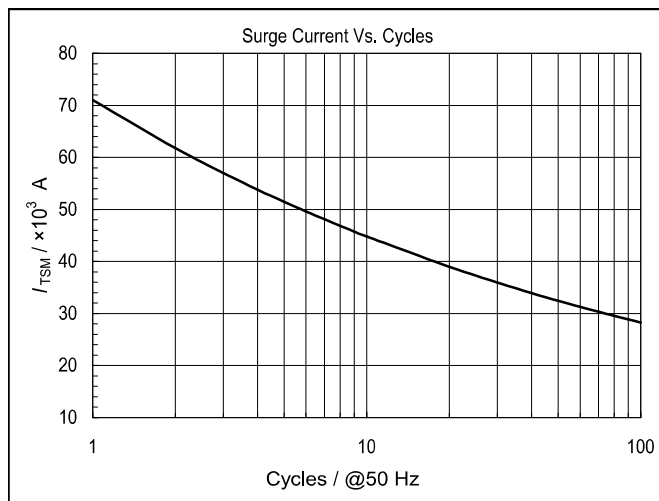


Fig3. Surge Current Vs. Cycles

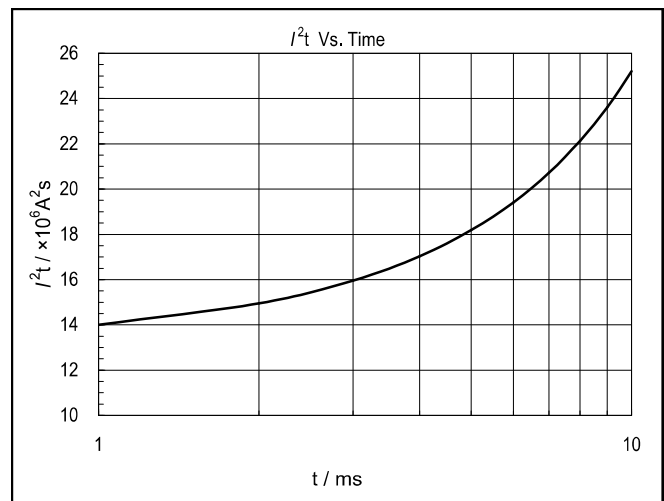


Fig4. I²t Vs. Time

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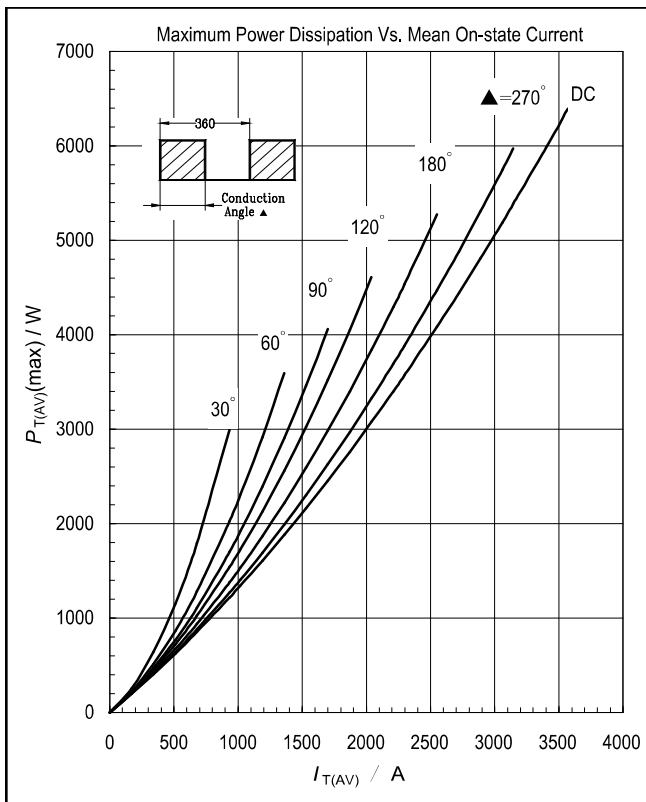


Fig5. Maximum Power Dissipation Vs. Mean On-state Current

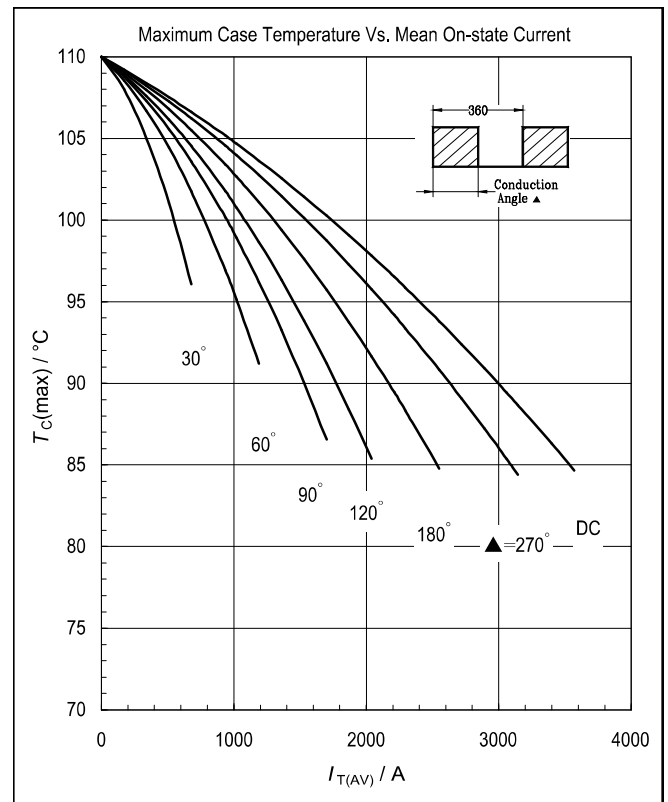


Fig6. Maximum Case Temperature Vs. Mean On-state Current

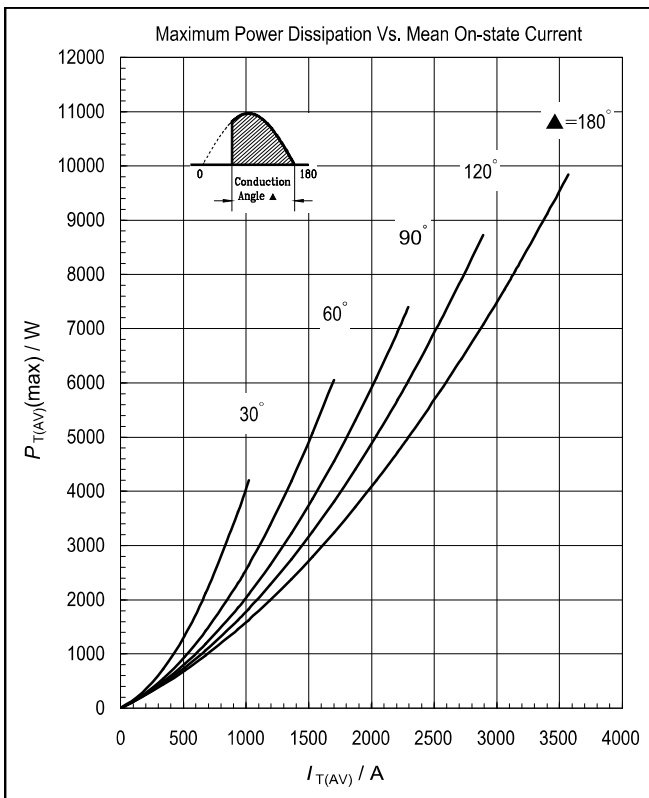


Fig7. Maximum Power Dissipation Vs. Mean On-state Current

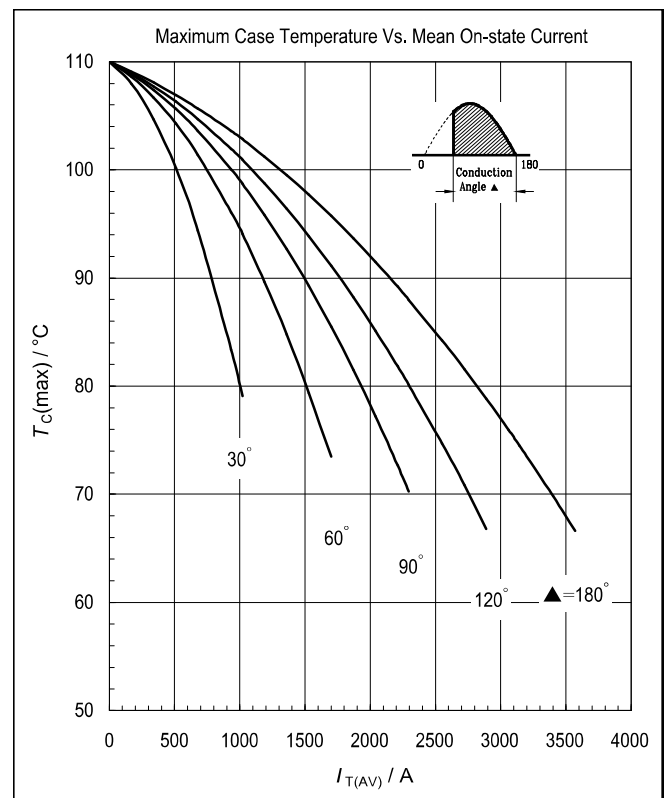


Fig8. Maximum Case Temperature Vs. Mean On-state Current

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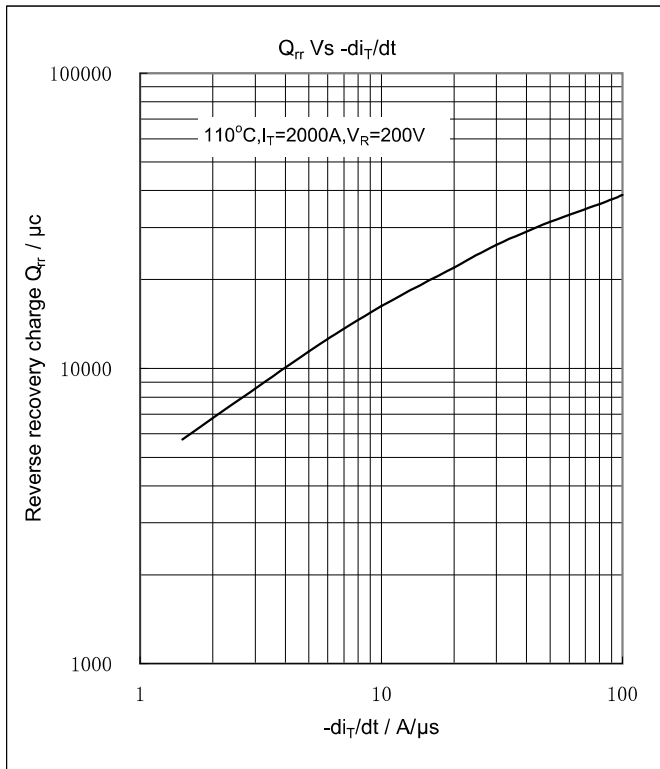


Fig9. Reverse recovery charge Vs. $-di_T/dt$

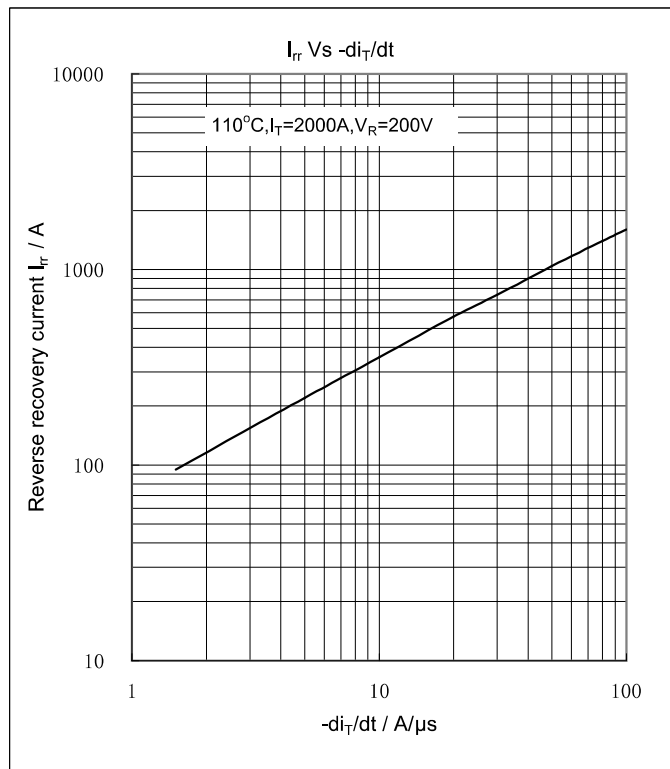


Fig10. Reverse recovery current Vs. $-di_T/dt$

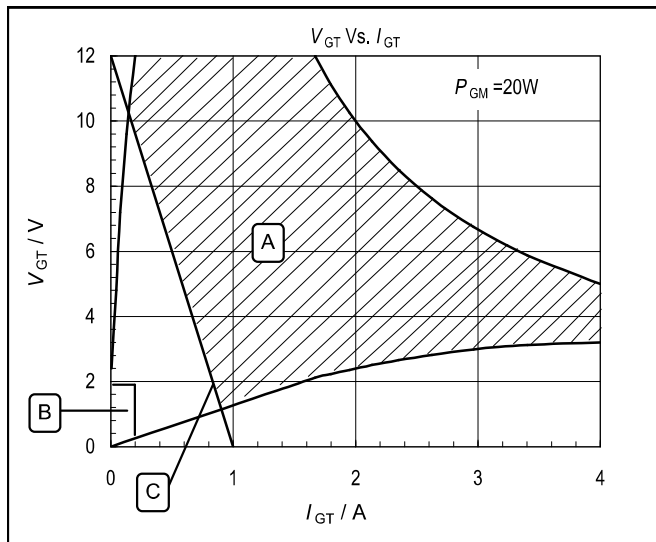


Fig11. V_{GT} Vs. I_{GT}

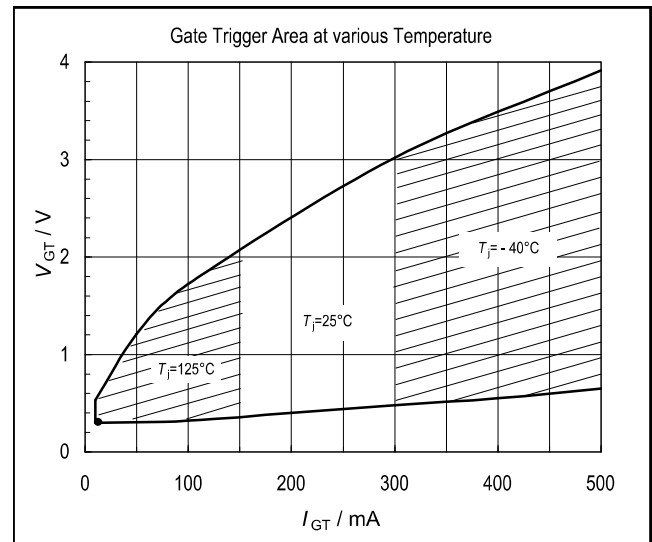


Fig12. Gate Trigger Area at various Temperature

A is Recommended Triggering Area.

B is Unreliable Triggering Area.

C is Recommended Gate Load Line.